

First Name	Last Name	Affiliation	Country/Region	Topic
Kazuhiko	Endo	National Institute of Advanced Industrial Science and Technology(AIST)	Japan	
Miaomiao	Wang	IBM	USA	Hot carrier reliability in ultra-scaled RMG SiGe SiGe P-in FET.
Yingchieh	Ho	National Don Hwa University	Taiwan	Energy-efficient standby-current suppression with bootstrapped power-gating technique
An	Chen	Global Foundries	USA	Cooptimization of emerging devices and architectures for energy-efficient computing
Choonghyun	Lee	IBM Research	USA	Interface Engineering of Si1-xGex Gate Stacks for High Performance Dual Channel CMOS
Kiat Seng	Yeo	SUTD	Singapore	Micro-LED structure and driver for display and communication
Toshiro	Hiramoto	University of Tokyo	Japan	Parallel Programmable Nonvolatile Memory Using SRAM Cells
Jie	Liu	Synopsys	China	Multiscale simulation of non-volatile Phase Change Memory
Rui	Zhang	Zhejiang University	China	
Kazuo	Tsutsui	Tokyo Institute of Technology	Japan	3D Scaling for Insulated Gate Bipolar Transistors (IGBTs) with Low Vce(sat)
Francis	Balestra	Grenoble INP-Minatec / Sinano Institute	France	Ultra low power and high performance nanoelectronic devices
Fengwei	An	Hiroshima University	Japan	Object-recognition VLSI for pedestrian detection in automotive applications
Jan Ven der	Spiegel	University of Pennsylvania	USA	
Kwang-Hyun	Baek	Chung-Ang University	Korea	The Trend in the Design of Direct-Digital Frequency Synthesizers (DDS
Wenzhong	Bao	Fudan University	China	
Mansun	Chan	Hong Kong University of Science & Technology	Hong Kong	A Universal Approach for Signal Dependent Circuit Reliability Simulation
Meng-Fan	Chang	National Tsing Hua University	Taiwan	Challenges in Circuit Designs for Nonvolatile Logics and Neuromorphic Computing Using_Memristors and STT-MRAMs_
Edward Y	Chang	National Chiao Tung University	Taiwan	Performance improvement of InGaAs FinFET Using NH3 treatment
C.Y.	Chang	National Academy of Engineering, U.S.A./National Chiao-Tung University	USA/Taiwan	More Moores :The first principle deduced negative Capacitance high Speed flash memory (1000X) and FET with SS <31mV/dec ,Vdd<0.1V and Low fricker Noise
Kuan-Neng	Chen	NCTU	Taiwan	Research Advances and Applications of 3D Integration

Yuhua	Cheng	Peking University	China	
Baoyong	Chi	Tsinghua University	China	Digital Polar Transmitters for IoT Applications
T.K.	Chiang	National Univ. of Kaohsiung	Taiwan	A New Device-Physics-Based DC Power Model for Junctionless Double-Gate MOSFET Working on Low-Power CMOS Subthreshold Logic Gates
Tao	Chu	Zhejiang University	China	Advanced Interconnection Technology, High K/Metal gate technology and other VLSI New Processing, New technologies
Yann	Deval	University of Bordeaux	France	Topic [2]: RF circuits (frequency generators)
Minoru	Fujishima	Hiroshima University	Japan	Terahertz CMOS Transceiver for Tera-bps Wireless Link
Xiaowu	Gong	Infineon Technologies Asia Pacific Pte Ltd		SWITCHING POWER CONVERTER FOR PRIMARY SIDE REGULATOR OR BUCK TOPOLOGY HAVING OPTIMAL DYNAMIC LOAD RESPONSE WITH ULTRA-LOW NOT LOAD POWER CONSUMPTION
Jifa	Hao	Fairchild Semiconductor	USA	
Minghui	Hong	National University of Singapore	Singapore	
Qingan	Huang	Southeast University	China	Towards an LC passive wireless sensor platform
Shyh-Jye	Jou	National Chiao Tung University	Taiwan	Baseband Processing Circuits and Systems for future 5G Communications in mmW Band
Jinfeng	Kang	Peking University	China	RRAM Based Novel Computing Paradigm and Application for Efficient Information Processing Systems
Haruo	Kobayashi	Gunma University	Japan	Fundamental Design Tradeoff and Performance Limit of Electronic Circuits Based on Uncertainty Relationships
ChaoSung	Lai	Chang Gung University	Taiwan	Nonvolatile Memory with 2D Materials for Floating Storage
Chaojiang	Li	Globe Foundry	USA	5G FEM Design with Advanced SOI Process
Yong	Lian	National University of Singapore	Singapore	
Dongsheng	Ma	University of Texas at Dallas	USA	Design techniques for high power density integrated switched capacitor power converters
Tapas Kumar	Maiti	Hiroshima University	Japan	Compact Modeling Approach for Electro-Mechanical System Simulation
Akira	Matsuzawa	Tokyo Institute of Technology	Japan	Data converters (ADCs and DACs)

Wai Tung	Ng	University of Toronto	Canada	A smart IGBT gate driver
Koji	Nii	Renesas Electronics Corporation	Japan	Silicon-on-Thin-BOX (SOTB) SRAM, or embedded TCAM design
Nobuyuki	Otsuka	Panasonic Corporation	Japan	Recent Progress in GaN Devices for Power and Integrated Circuit
David	Pan	Texas University at Austin	USA	TBD
Xiaodong	Pi	Zhejiang University	China	Printable silicon-quantum-dot materials and optoelectronic devices
Youhua	Shi	Waseda University	Japan	Approximate computing or Soft error tolerant design
Gerald	Sobelman	University of Minnesota	USA	Stochastic Computing Implementations
Litao	Sun	Southeast University	China	In-situ nanotechnology and nanodevices
Sheldon	Tan	University of California, Riverside	USA	
He	Tang	UESTC	USA	
Tian-Shen	Tang	SMIC	China	eNVM Technology for Intelligent Device Applications: Opportunities, Challenges and Solutions
Zhihua	Wang	Tsinghua University	China	A System Architecture of a Smart Binaural Hearing Aid Using a Mobile Computing Platform
C.C.	Wang	National Sun Yat Sun University	Taiwan	
Jer Chyi	Wang	Chang Gung University	Taiwan	
Runsheng	Wang	Peking University	China	Variability-aware and reliability-aware design for nanoscale FinFET technology
Xiaoqing	Wen	Kyushu Institute of Technology	Japan	Power-Aware Testing of Low-Power LSI Circuits
Hei	Wong	City University of Hong Kong	Hong Kong	CMOS Charge Pump for RF Energy Harvesting Applications
Ngai	Wong	University of HK	Hong Kong	Some Applications of Tensor Networks in Electronic Design
Jason	Woo	University of California, Los Angeles	USA	
Yanqing	Wu	Huazhong Univ. of Science and Technology	China	High Performance Transistors based on two dimensional materials
Andy	Wu	NTU	Taiwan	
Wang	Yang	College of Science Heilongjiang University of Science and Technology	China	Structural analysis of Al-Ni-Co quasicrystals

Yuchao	Yang	Peking University	China	Memristors for Emerging Memory and Computing Applications
Kiat Seng	Yeo	SUTD, Nanyang Technological University	Singapore	RF Mixer design techniques using GaAs process
You	Yin	Gunma University	Japan	Phase-change memory
Hao	Yu	Nanyang Technological University	Singapore	CMOS nanopore circuit for DNA sequencing'
HongYu	Yu	Nanyang Technological University	Singapore	Advanced GaN HEMT devices
Wenjian	Yu	Tsinghua University	China	
Bei	Yu	Chinese University of HK	Hong Kong	VLSI Layout Hotspot Detection : From Feature Learning to Deep Learning
Weidong	Zhang	Liverpool John Moores University	UK	Switching and failure mechanisms in non-filamentary (a-VMCO) RRAM devices
Bo	Zhang	University of Electronic Science and Technology of China	China	Ultralow Power Loss Integratable High-voltage MOSFETs.
J.F.	Zhang	Liverpool John Moores University	UK	Hot carrier aging and positive bias temperature instability: defects, variations, and lifetime prediction
Haixia	Zhang	Peking University	China	High Performance Energy Harvester for Portable Electronics
Weisheng	Zhao	Univ. Paris-Sud, Orsay	France	Spin Orbit Torque Fast Magnetic Random Access Memory
Jun	Zhou	Institute of Microelectronics, A*STAR	Singapore	Near-threshold Processor Design Techniques for Intelligent Sensing
Pingqiang	Zhou	Shanghai Tech University	China	Runtime Optimization of On-Chip Decoupling Capacitors for Leakage Power Reduction
Rui	Wu	Tokyo Institute of Technology	Japan	Ultra-high-data-rate 60-GHz CMOS Transceiver for Future Radio Access Network
Patricia	Desgreys	Telecom ParisTech	France	Wideband Power Amplifier linearization: challenges, solutions and trends
Andreas	Kaiser	Univ. Lille,	France	Digital RF transmitter architectures exploiting semi-digital FIRDACs in various configurations
Kazutoshi	Kobayashi	Kyoto Institute of Technology	Japan	Highly-reliable integrated circuits for ground and space applications
Lan	Wei	Univ. of Waterloo	Canada	
Domenico	Rossi	ST	Italy	Looking back and forward: the execution dilemma and the importance of innovation in the semiconductor industry
Wenjuan	Zhu	University of Illinois at Urbana-Champaign	USA	Two-dimensional Materials and Nanoscale Electronic Devices